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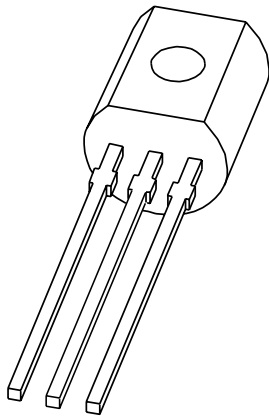
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DATA SHEET



BC549; BC550 NPN general purpose transistors

Product data sheet
Supersedes data of 1999 Apr 22

2004 Oct 11

NPN general purpose transistors

BC549; BC550

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

APPLICATIONS

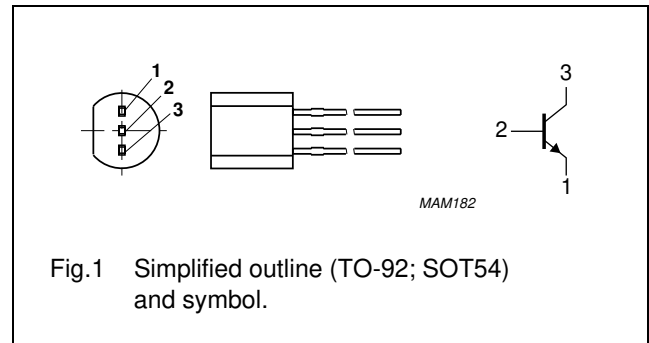
- Low noise stages in audio frequency equipment.

DESCRIPTION

NPN transistor in a TO-92; SOT54 plastic package.
PNP complements: BC559 and BC560.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BC549C	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54
BC550C			

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BC549		–	30	V
	BC550		–	50	V
V_{CEO}	collector-emitter voltage	open base			
	BC549		–	30	V
	BC550		–	45	V
V_{EBO}	emitter-base voltage	open collector	–	5	V
I_C	collector current (DC)		–	100	mA
I_{CM}	peak collector current		–	200	mA
I_{BM}	peak base current		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	500	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	250	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

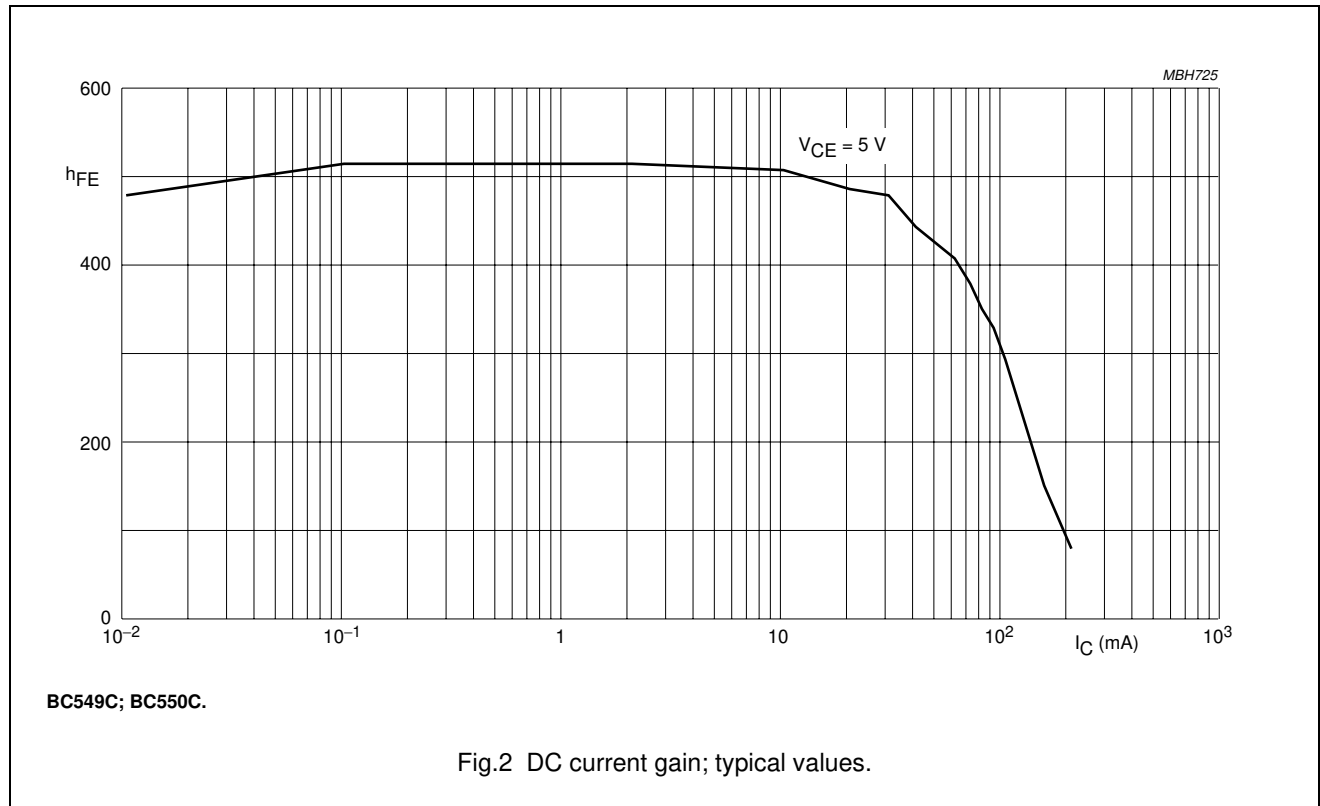
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{CB} = 30\text{ V}; I_E = 0\text{ A}$	–	–	15	nA
		$V_{CB} = 30\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ °C}$	–	–	5	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	–	–	100	nA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}$; see Fig.2 $I_C = 10\text{ }\mu\text{A}$ $I_C = 2\text{ mA}$	– 420	270 520	– 800	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	90	250	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	–	200	600	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$; note 1	–	700	–	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$; note 1	–	900	–	mV
V_{BE}	base-emitter voltage	$V_{CE} = 5\text{ V}; I_C = 2\text{ mA}$; note 2	580	660	700	mV
		$V_{CE} = 5\text{ V}; I_C = 10\text{ mA}$; note 2	–	–	770	mV
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_C = 0\text{ A};$ $f = 1\text{ MHz}$	–	1.5	–	pF
C_e	emitter capacitance	$V_{EB} = 0.5\text{ V}; I_C = I_E = 0\text{ A};$ $f = 1\text{ MHz}$	–	11	–	pF
f_T	transition frequency	$V_{CE} = 5\text{ V}; I_C = 10\text{ mA};$ $f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure	$V_{CE} = 5\text{ V}; I_C = 200\text{ }\mu\text{A};$ $R_S = 2\text{ k}\Omega; f = 10\text{ Hz to }15.7\text{ kHz}$	–	–	4	dB
		$V_{CE} = 5\text{ V}; I_C = 200\text{ }\mu\text{A};$ $R_S = 2\text{ k}\Omega; f = 1\text{ kHz}; B = 200\text{ Hz}$	–	–	4	dB

Notes

1. V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.
2. V_{BE} decreases by about 2 mV/K with increasing temperature.

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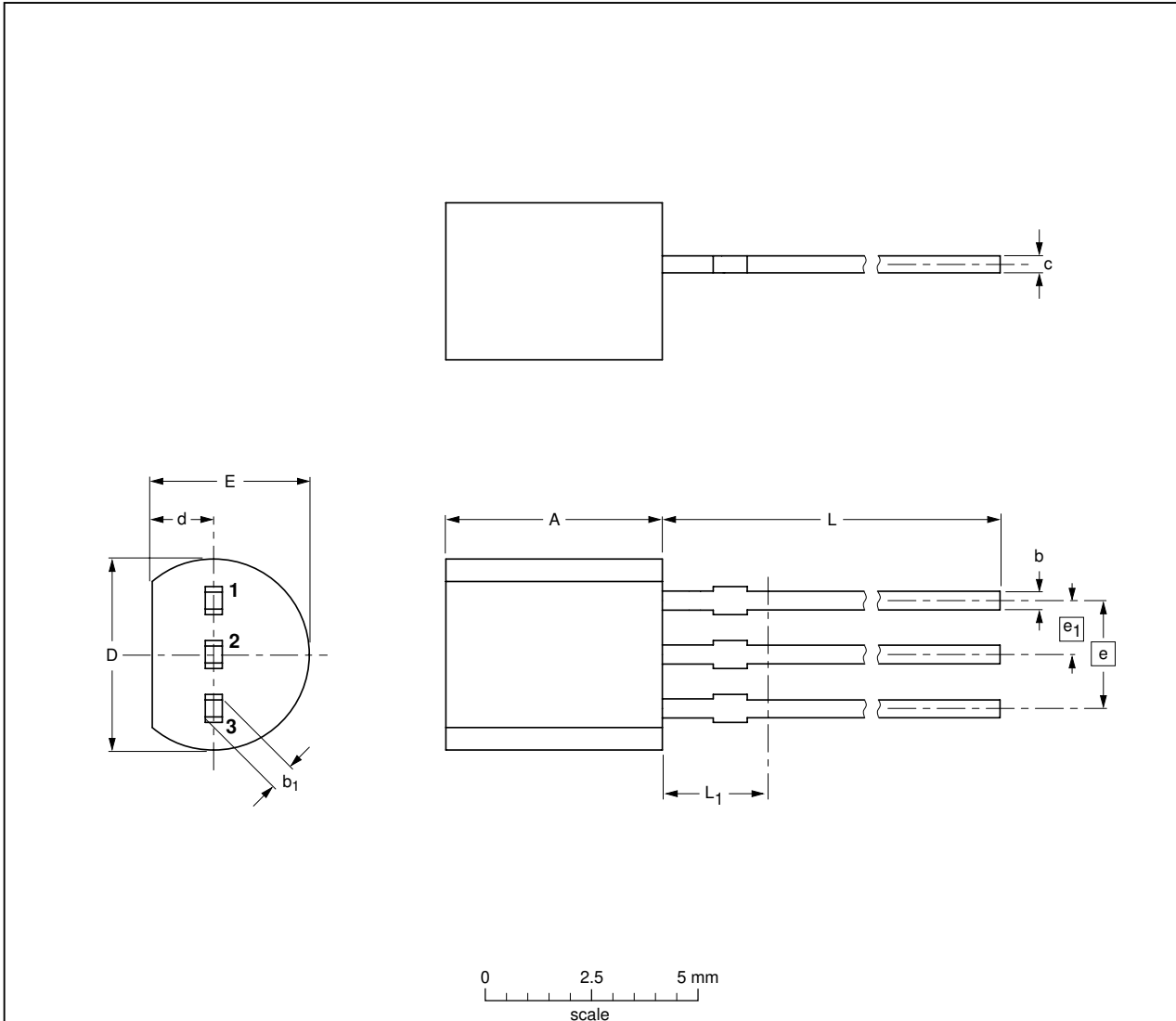
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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b ₁	c	D	d	E	e	e ₁	L	L ₁ ⁽¹⁾ max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT54		TO-92	SC-43A		04-06-28 04-11-16

NPN general purpose transistors

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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